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Cncl'd*

2. (Amended) The surface acoustic wave device according to claim 1, wherein a depth of the region is not more than 50 nm.
3. (Amended) The surface acoustic wave device according to claim 1, wherein the region has a lower resistance than that of an inner portion of the substrate.
4. (Twice Amended) The surface acoustic wave device according to claim 3, wherein a sheet resistance of the region ranges from  $10^8 \Omega/\text{square}$  to  $10^{15} \Omega/\text{square}$ .
5. (Twice Amended) The surface acoustic wave device according to claim 23, wherein the substance is at least one selected from the group consisting of a reducing gas, silane, nitrogen, oxygen, argon, silicon, arsenic, boron, phosphorus, tin, indium, chromium, tantalum, molybdenum, germanium, and nickel.

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Please add new claim 23 as follows.

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23. (New) The surface acoustic wave device according to claim 1, wherein a substance in at least one form selected from the group consisting of atoms, molecules, clusters, ions and radicals is added to the substrate in the region.